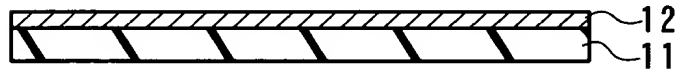


*Fig. 1*

*Fig. 2a*



*Fig. 2b*

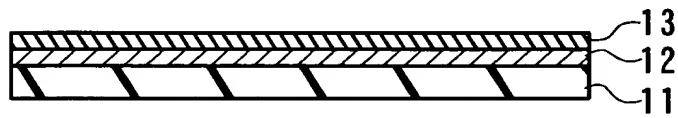
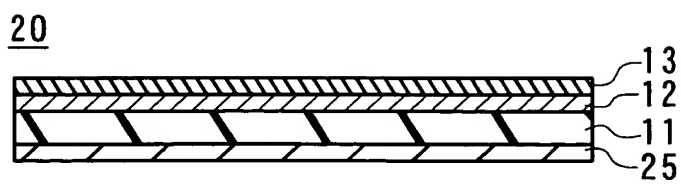
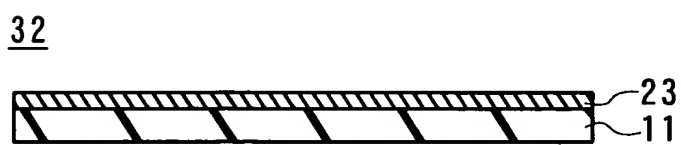


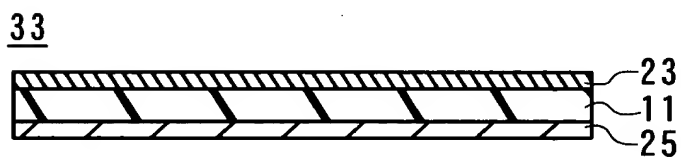
FIG. 3



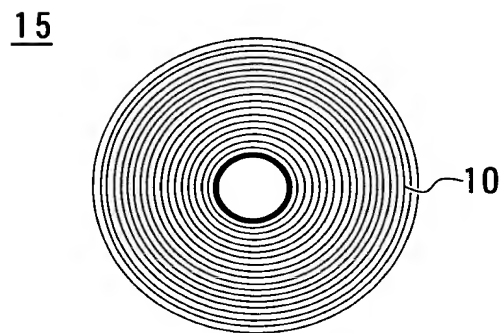
*Fig. 3*



*Fig. 4*



*Fig. 5*



*Fig. 6*

Figure 1 is a cross-sectional view of a semiconductor device 10. The device includes a substrate 11, a thin layer 12, and a thicker layer 13. A patterned layer 16 is formed on top of layer 13, and rectangular features 17 are formed on top of layer 16.

A cross-sectional view of a semiconductor device. It shows a substrate 16 with a thin layer 18 on its top surface. Above layer 18 is a stack of three layers: 11, 12, and 13, which are grouped by a bracket 10. On top of this stack is a patterned layer 17, represented by black rectangular blocks.

Fig. 7c

FIG. 8

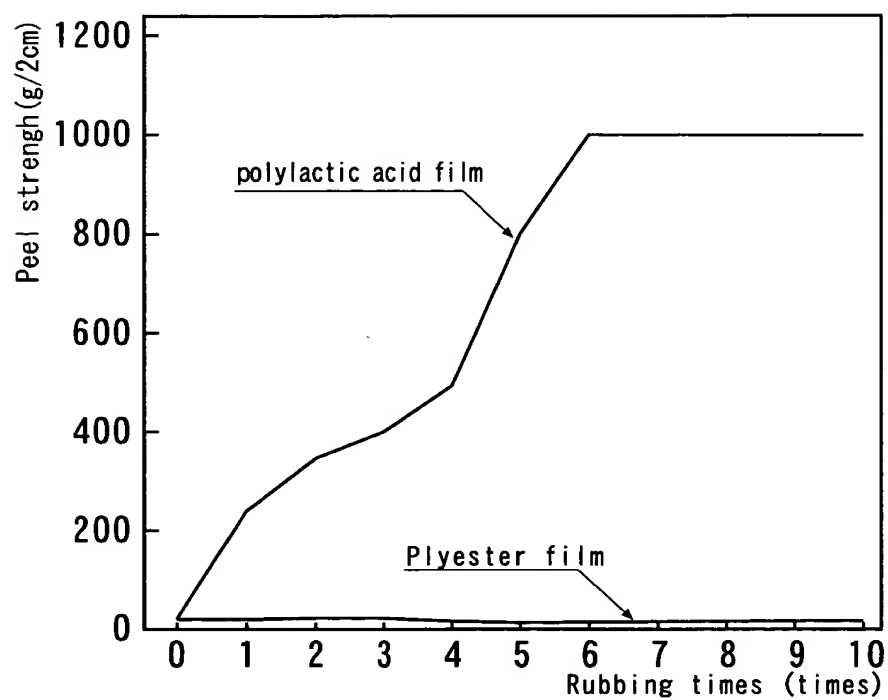


Fig. 8

Fig. 9a

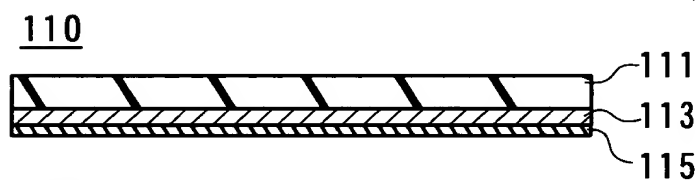


Fig. 9b

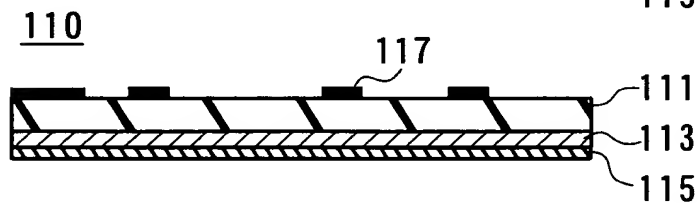


Fig. 9c

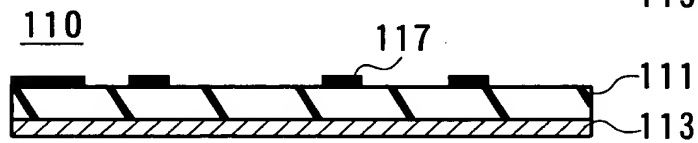


Fig. 9d

